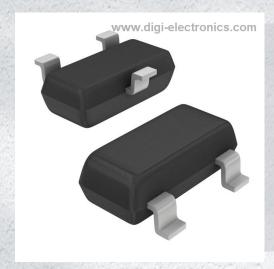


2N7002LT7H Datasheet



https://www.DiGi-Electronics.com

DiGi Electronics Part Number 2N7002LT7H-DG

Manufacturer onsemi

Manufacturer Product Number 2N7002LT7H

Description MOSFET N-CH 60V 115MA SOT23-3

Detailed Description N-Channel 60 V 115mA (Tc) 225mW (Ta) Surface Mo

unt SOT-23-3 (TO-236)



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

DiGi is a global authorized distributor of electronic components.



Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
2N7002LT7H	onsemi
Series:	Product Status:
	Active
FET Type:	Technology:
N-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
60 V	115mA (Tc)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ Id, Vgs:
5V, 10V	7.50hm @ 500mA, 10V
Vgs(th) (Max) @ ld:	Vgs (Max):
2.5V @ 250μA	±20V
Input Capacitance (Ciss) (Max) @ Vds:	FET Feature:
50 pF @ 25 V	
Power Dissipation (Max):	Operating Temperature:
225mW (Ta)	-55°C ~ 150°C (TJ)
Grade:	Qualification:
Automotive	AEC-Q101
Mounting Type:	Supplier Device Package:
Surface Mount	SOT-23-3 (TO-236)
Package / Case:	Base Product Number:
TO-236-3, SC-59, SOT-23-3	2N7002

Environmental & Export classification

8541.21.0095

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	



MOSFET - N-Channel, Small Signal, SOT-23

60 V, 115 mA

2N7002L, 2V7002L

Features

- 2V Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable (2V7002L)
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	60	Vdc
Drain-Gate Voltage ($R_{GS} = 1.0 M\Omega$)	V_{DGR}	60	Vdc
Drain Current - Continuous $T_C = 25^{\circ}C$ (Note 1) $T_C = 100^{\circ}C$ (Note 1) - Pulsed (Note 2)	I _D I _D I _{DM}	±115 ±75 ±800	mAdc
Gate-Source Voltage - Continuous - Non-repetitive (t _p ≤ 50 μs)	V _{GS} V _{GSM}	±20 ±40	Vdc Vpk

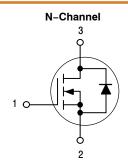
THERMAL CHARACTERISTICS

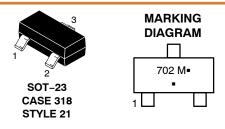
Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 3) T _A = 25°C Derate above 25°C Thermal Resistance, Junction-to-Ambient	P_D	225 1.8 556	mW mW/°C °C/W
Total Device Dissipation (Note 4) Alumina Substrate, T _A = 25°C Derate above 25°C Thermal Resistance, Junction–to–Ambient	P_D	300 2.4 417	mW mW/°C °C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- The Power Dissipation of the package may result in a lower continuous drain current.
- 2. Pulse Test: Pulse Width \leq 300 $\mu s,$ Duty Cycle \leq 2.0%.
- 3. $FR-5 = 1.0 \times 0.75 \times 0.062$ in.
- 4. Alumina = $0.4 \times 0.3 \times 0.025$ in 99.5% alumina.

V _{(BR)DSS}	R _{DS(on)} MAX	I _D MAX
60 V	7.5 Ω @ 10 V, 500 mA	115 mA





702 = Device Code

M = Date Code*

■ Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]	
2N7002LT1G		3,000 Tape & Reel	
2N7002LT3G	SOT-23 (Pb-Free)	10,000 Tape & Reel	
2N7002LT7G		3,500 Tape & Reel	
2V7002LT1G		3,000 Tape & Reel	
2V7002LT3G	SOT-23 (Pb-Free)	10,000 Tape & Reel	
2N7002LT1H*		3,000 Tape & Reel	
2N7002LT7H*		3,500 Tape & Reel	

- †For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
- *Not for new design.

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2N7002L, 2V7002L

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS	•		•	•	•
Drain-Source Breakdown Voltage (V _{GS} = 0, I _D = 10 μAdc)	V _{(BR)DSS}	60	_	-	Vdc
Zero Gate Voltage Drain Current $T_J = 25^{\circ}C$ $(V_{GS} = 0, V_{DS} = 60 \text{ Vdc})$ $T_J = 125^{\circ}C$	I _{DSS}	- -	_ _	1.0 500	μAdc
Gate-Body Leakage Current, Forward (V _{GS} = 20 Vdc)	I _{GSSF}	-	-	100	nAdc
Gate-Body Leakage Current, Reverse (V _{GS} = -20 Vdc)	I _{GSSR}	-	-	-100	nAdc
ON CHARACTERISTICS (Note 5)	•		•	•	•
Gate Threshold Voltage ($V_{DS} = V_{GS}$, $I_D = 250 \mu Adc$)	V _{GS(th)}	1.0	_	2.5	Vdc
On–State Drain Current $(V_{DS} \ge 2.0 \ V_{DS(on)}, \ V_{GS} = 10 \ Vdc)$	I _{D(on)}	500	-	-	mA
Static Drain–Source On–State Voltage (V_{GS} = 10 Vdc, I_D = 500 mAdc) (V_{GS} = 5.0 Vdc, I_D = 50 mAdc)	V _{DS(on)}	- -	- -	3.75 0.375	Vdc
$ \begin{array}{llllllllllllllllllllllllllllllllllll$	r _{DS(on)}	- - - -	- - - -	7.5 13.5 7.5 13.5	Ohms
Forward Transconductance ($V_{DS} \ge 2.0 \ V_{DS(on)}$, $I_D = 200 \ mAdc$)	9FS	80	_	-	mS
DYNAMIC CHARACTERISTICS	•		•	•	•
Input Capacitance ($V_{DS} = 25 \text{ Vdc}, V_{GS} = 0, f = 1.0 \text{ MHz}$)	C _{iss}	-	_	50	pF
Output Capacitance $(V_{DS} = 25 \text{ Vdc}, V_{GS} = 0, f = 1.0 \text{ MHz})$	C _{oss}	_	_	25	pF
Reverse Transfer Capacitance $(V_{DS} = 25 \text{ Vdc}, V_{GS} = 0, f = 1.0 \text{ MHz})$	C _{rss}	-	_	5.0	pF
SWITCHING CHARACTERISTICS (Note 5)			•		•
Turn–On Delay Time $(V_{DD} = 25 \text{ Vdc}, I_D \cong 500 \text{ mAdc},$	t _{d(on)}	_	-	20	ns
Turn–Off Delay Time $R_G = 25 \Omega$, $R_L = 50 \Omega$, $V_{gen} = 10 V$)	t _{d(off)}	-	-	40	ns
BODY-DRAIN DIODE RATINGS	•				
Diode Forward On-Voltage (I _S = 115 mAdc, V _{GS} = 0 V)	V_{SD}	-	_	-1.5	Vdc
Source Current Continuous (Body Diode)	I _S	-	_	-115	mAdc
Source Current Pulsed	I _{SM}	-	-	-800	mAdc

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.



2N7002L, 2V7002L

TYPICAL ELECTRICAL CHARACTERISTICS

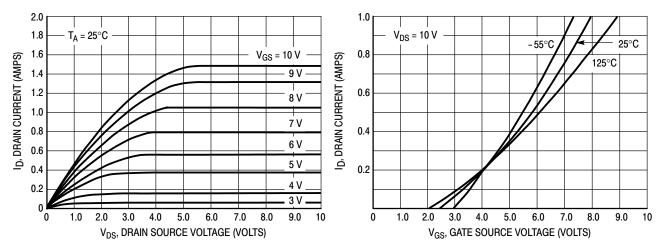


Figure 1. Ohmic Region

Figure 2. Transfer Characteristics

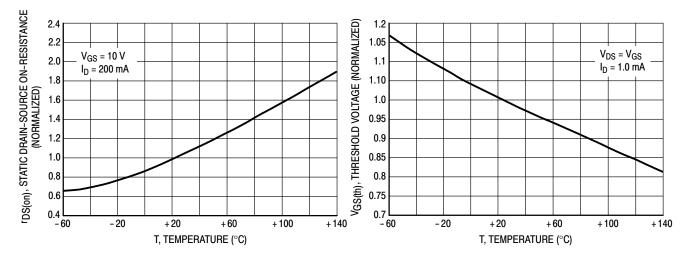


Figure 3. Temperature versus Static Drain-Source On-Resistance

Figure 4. Temperature versus Gate Threshold Voltage



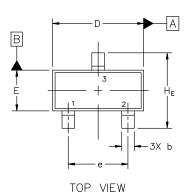
MECHANICAL CASE OUTLINE

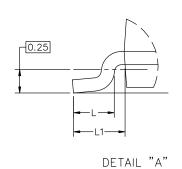
PACKAGE DIMENSIONS



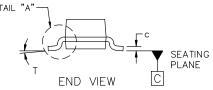
SOT-23 (TO-236) 2.90x1.30x1.00 1.90P **CASE 318 ISSUE AU**

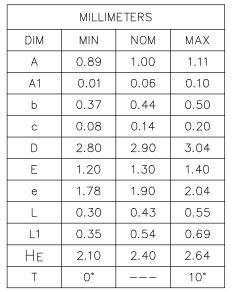
DATE 14 AUG 2024





DETAIL "A'





NOTES:

- DIMENSIONING AND TOLERANCING 1.
- PER ASME Y14.5M, 2018. CONTROLLING DIMENSIONS: MILLIMETERS.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE
- BASE MATERIAL.
 DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

GENERIC MARKING DIAGRAM*

SIDE VIEW

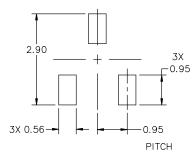


XXX = Specific Device Code

= Date Code

= Pb-Free Package

^{*}This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "=", may or may not be present. Some products may not follow the Generic Marking.



Scale 3:1

RECOMMENDED MOUNTING FOOTPRINT

* For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

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DATE 14 AUG 2024

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE	ı	
STYLE 9:	STYLE 10:	STYLE 11: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE	STYLE 12:	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN		PIN 1. CATHODE	PIN 1. SOURCE	PIN 1. CATHODE
2. ANODE	2. SOURCE		2. CATHODE	2. DRAIN	2. GATE
3. CATHODE	3. GATE		3. ANODE	3. GATE	3. ANODE
STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:	STYLE 19:	STYLE 20:
PIN 1. GATE	PIN 1. ANODE	PIN 1. NO CONNECTION	PIN 1. NO CONNECTION	PIN 1. CATHODE	PIN 1. CATHODE
2. CATHODE	2. CATHODE	2. ANODE	2. CATHODE	2. ANODE	2. ANODE
3. ANODE	3. CATHODE	3. CATHODE	3. ANODE	3. CATHODE-ANODE	3. GATE
STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
2. SOURCE	2. OUTPUT	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3. DRAIN	3. INPUT	3. CATHODE	3. SOURCE	3. GATE	3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

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